

Application Serial No.: 10/780,341
Attorney Docket No.: BUR920000061US1

AMENDMENTS TO THE CLAIMS

The status of the claims of the present application stands as follows:

Claims 1-18 (Canceled)

19. **(Currently Amended)** A method for scrubbing an exhaust gas of a manufacturing process, the exhaust gas comprising a first chemical component and a second chemical component, comprising the steps of:
- a. flowing the exhaust gas through an enclosure defining a chamber and containing at least one substrate;
 - b. baffling, using said at least one substrate, the exhaust gas within said chamber so as to increase the residence time of the exhaust gas within said chamber; and
 - ~~bc.~~ causing the first chemical component to be chemical vapor deposited onto said at least one substrate.
20. **(Currently Amended)** A method according to claim 19, further comprising the step of removing the second chemical component from the exhaust gas after performing step ~~bc~~.
21. **(Currently Amended)** A method according to claim 19, wherein step ~~bc~~ is performed by heating at least one of said at least one substrate and said enclosure to at least 800°C.
22. **(Currently Amended)** A method according to claim 21, wherein step ~~bc~~ is performed by heating at least one of said at least one substrate and said enclosure to at least 1100°C.
23. **(Original)** A method according to claim 19, wherein the first chemical component is non-toxic and the second chemical component is toxic.
24. **(Original)** A method according to claim 23, wherein the first chemical component comprises silicon and the second chemical component comprises arsenic.

Application Serial No.: 10/780,341
Attorney Docket No.: BUR920000061US1

25. **(Currently Amended)** A method according to claim 19, further comprising after step ~~b~~c) the steps of:
- removing said at least one substrate from said enclosure;
 - cleaning said at least one substrate of any film deposited thereon;
 - installing said at least one substrate in said enclosure; and
 - again causing the first chemical component to be chemical vapor deposited onto said at least one substrate.
26. **(New)** A method of scrubbing an exhaust gas of a manufacturing process, the exhaust gas comprising a carrier gas and an n-type dopant gas, comprising the steps of:
- flowing the exhaust gas through an enclosure defining a chamber and containing at least one substrate;
 - baffling, using said at least one substrate, the exhaust gas within said chamber so as to increase the residence time of the exhaust gas within said chamber; and
 - causing an n-doped layer of silicon to be chemical vapor deposited onto said at least one substrate.
27. **(New)** A method according to claim 26, further comprising the step of removing the n-type dopant gas from the exhaust gas after performing step c).
28. **(New)** A method according to claim 26, wherein step c) is performed by heating at least one of said at least one substrate and said enclosure to at least 800°C.
29. **(New)** A method according to claim 28, wherein step c) is performed by heating at least one of said at least one substrate and said enclosure to at least 1100°C.
30. **(New)** A method according to claim 26, wherein the carrier gas comprises silicon and the n-type dopant gas comprises arsenic.

Application Serial No.: 10/780,341
Attorney Docket No.: BUR920000061US1

31. (New) A method according to claim 26, wherein said at least one substrate has a plurality of apertures and step b) is performed by causing the exhaust gas to flow substantially only through said plurality of apertures.
32. (New) A method according to claim 26, wherein said enclosure contains a plurality of substrates arranged in series with one another along said chamber so as to baffle flow of the exhaust gas.
33. (New) A method according to claim 32, wherein said plurality of substrates are arranged within said chamber so as to cause the exhaust gas to flow along a substantially serpentine path within said chamber.
34. (New) A method according to claim 32, wherein each of said plurality of substrates comprises a plurality of apertures and step b) is performed by causing the exhaust gas to flow substantially only through said plurality of apertures of each of said plurality of substrates.
35. (New) A method according to claim 19, wherein said at least one substrate has a plurality of apertures and step b) is performed by causing the exhaust gas to flow substantially only through said plurality of apertures.
36. (New) A method according to claim 19, wherein said enclosure contains a plurality of substrates arranged in series with one another along said chamber so as to baffle flow of the exhaust gas.
37. (New) A method according to claim 36, wherein said plurality of substrates are arranged within said chamber so as to cause the exhaust gas to flow along a substantially serpentine path within said chamber.

Application Serial No.: 10/780,341
Attorney Docket No.: BUR920000061US1

38. (New) A method according to claim 36, wherein each of said plurality of substrates comprises a plurality of apertures and step b) is performed by causing the exhaust gas to flow substantially only through said plurality of apertures of each of said plurality of substrates.

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